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ON Semiconductor®

FQA10N80C-F109

N-Channel QFET® MOSFET

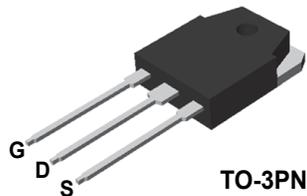
800 V, 10 A, 1.1 Ω

Features

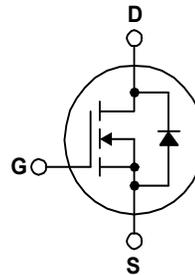
- 10 A, 800 V, $R_{DS(on)} = 1.1 \Omega$ (Max.) @ $V_{GS} = 10 V$, $I_D = 5 A$
- Low Gate Charge (Typ. 44 nC)
- Low C_{rss} (Typ. 15 pF)
- 100% Avalanche Tested
- RoHS compliant

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



TO-3PN



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FQA10N80C-F109	Unit
V_{DSS}	Drain to Source Voltage	800	V
I_D	Drain Current	-Continuous ($T_C = 25^\circ C$)	10
		-Continuous ($T_C = 100^\circ C$)	6.32
I_{DM}	Drain Current - Pulsed (Note 1)	40	A
V_{GSS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	920	mJ
I_{AR}	Avalanche Current (Note 1)	10	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	24	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$)	- Derate above $25^\circ C$	240
			1.92
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	FQA10N80C-F109	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.52	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	40	$^\circ C/W$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA10N80C-F109	FQA10N80C	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	800	--	--	V	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.98	--	$\text{V}/^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA	
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA	
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA	
On Characteristics							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.0\text{ A}$	--	0.93	1.1	Ω	
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 5.0\text{ A}$	--	5.8	--	S	
Dynamic Characteristics							
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2150	2800	pF	
C_{oss}	Output Capacitance		--	180	230	pF	
C_{riss}	Reverse Transfer Capacitance		--	15	20	pF	
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 10.0\text{ A},$ $R_G = 25\ \Omega$	--	50	110	ns	
t_r	Turn-On Rise Time		--	130	270	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note4)	--	90	190	ns
t_f	Turn-Off Fall Time		(Note4)	--	80	170	ns
Q_g	Total Gate Charge	$V_{DS} = 640\text{ V}, I_D = 10.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	45	58	nC	
Q_{gs}	Gate-Source Charge		(Note 4)	--	13.5	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	17	--	nC
Drain-Source Diode Characteristics and Maximum Ratings							
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	10.0	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	40.0	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 10.0\text{ A}$	--	--	1.4	V	
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 10.0\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	730	--	ns	
Q_{rr}	Reverse Recovery Charge		--	10.9	--	μC	

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. $L = 17.3\text{ mH}, I_{AS} = 10\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 8.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

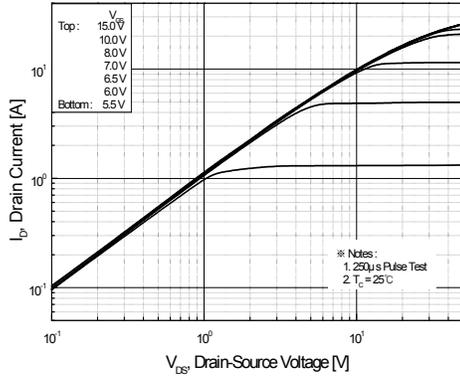


Figure 1. On-Region Characteristics

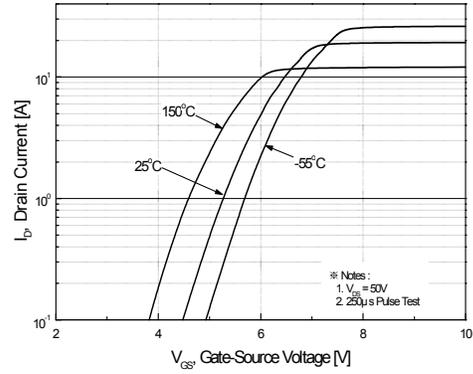


Figure 2. Transfer Characteristics

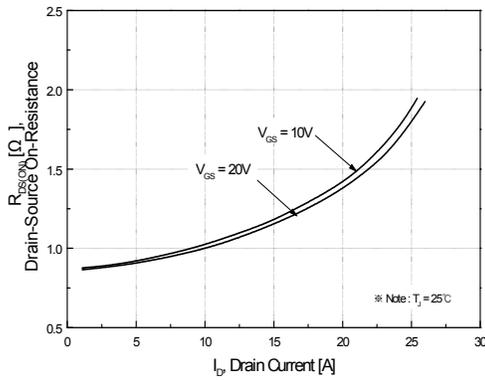


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

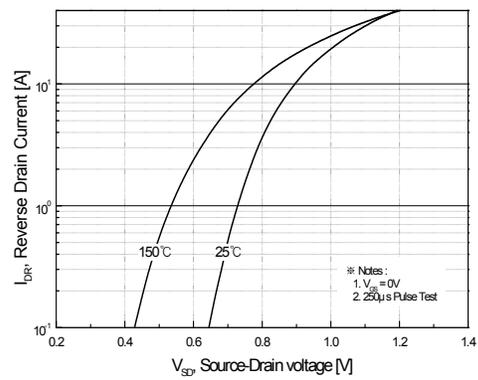


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

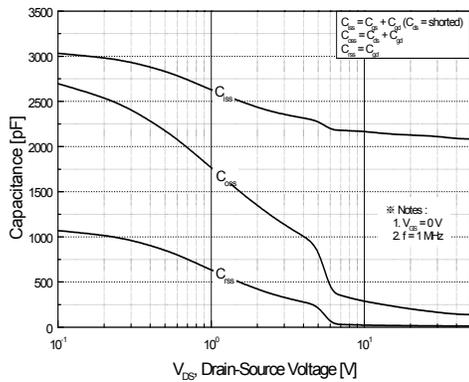


Figure 5. Capacitance Characteristics

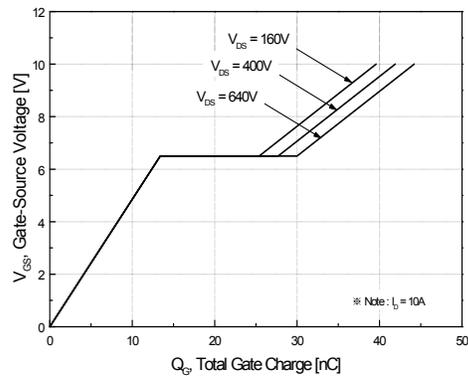


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

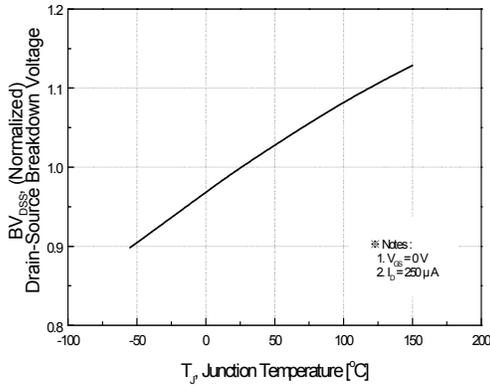


Figure 7. Breakdown Voltage Variation vs Temperature

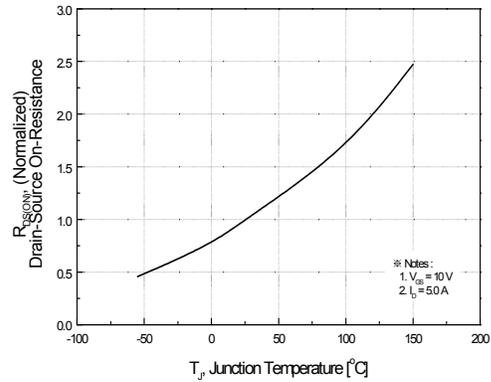


Figure 8. On-Resistance Variation vs Temperature

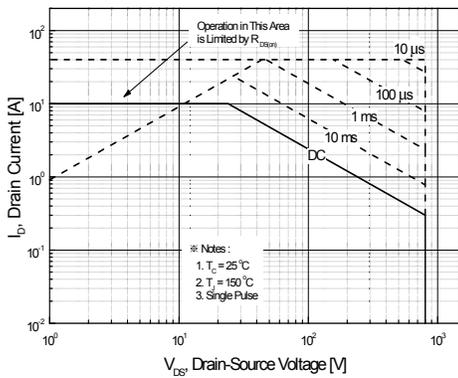


Figure 9. Maximum Safe Operating Area

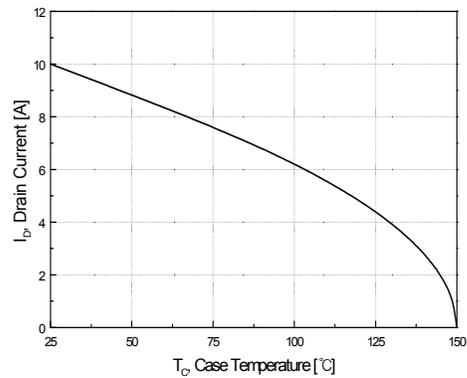


Figure 10. Maximum Drain Current vs Case Temperature

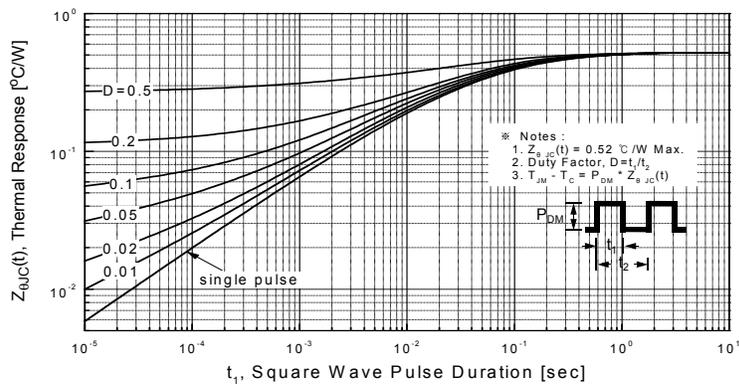


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

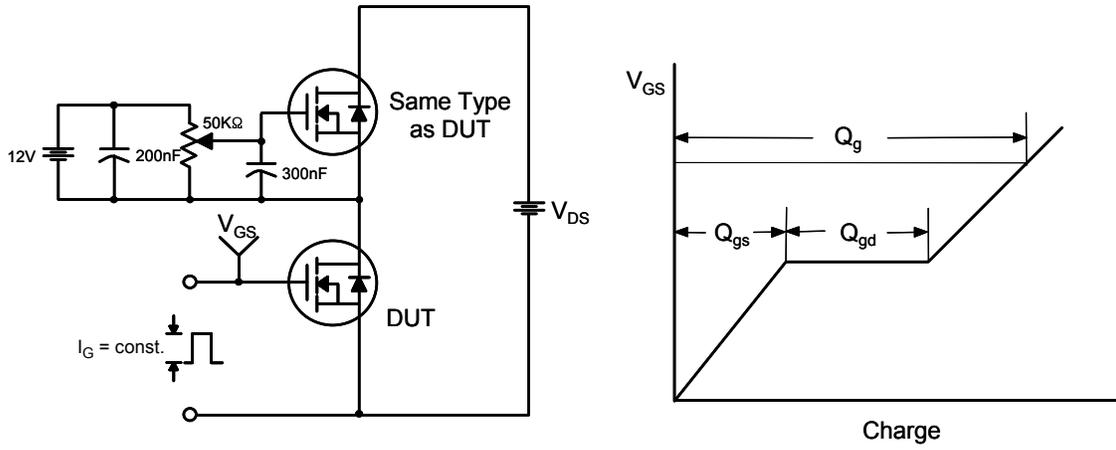


Figure 13. Resistive Switching Test Circuit & Waveforms

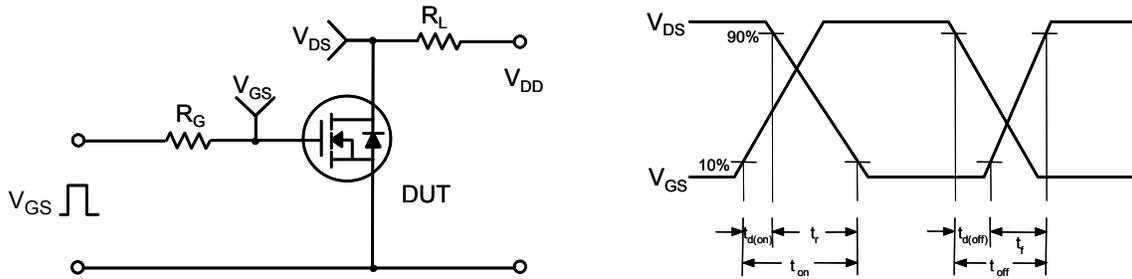


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

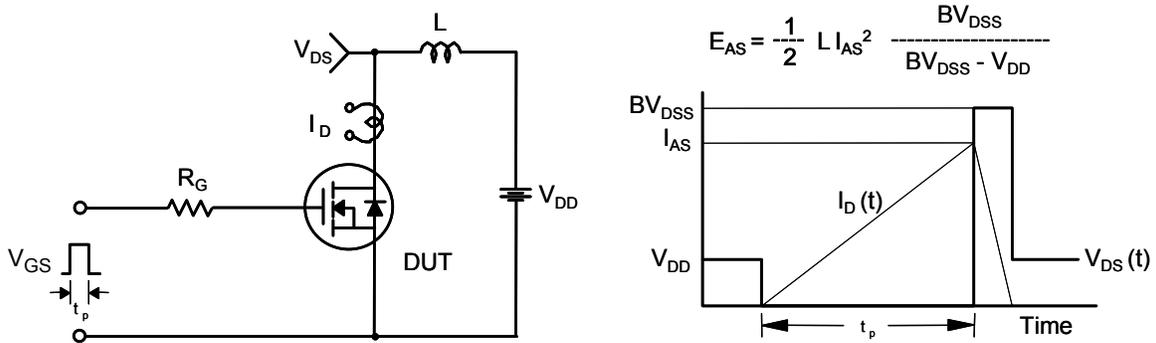
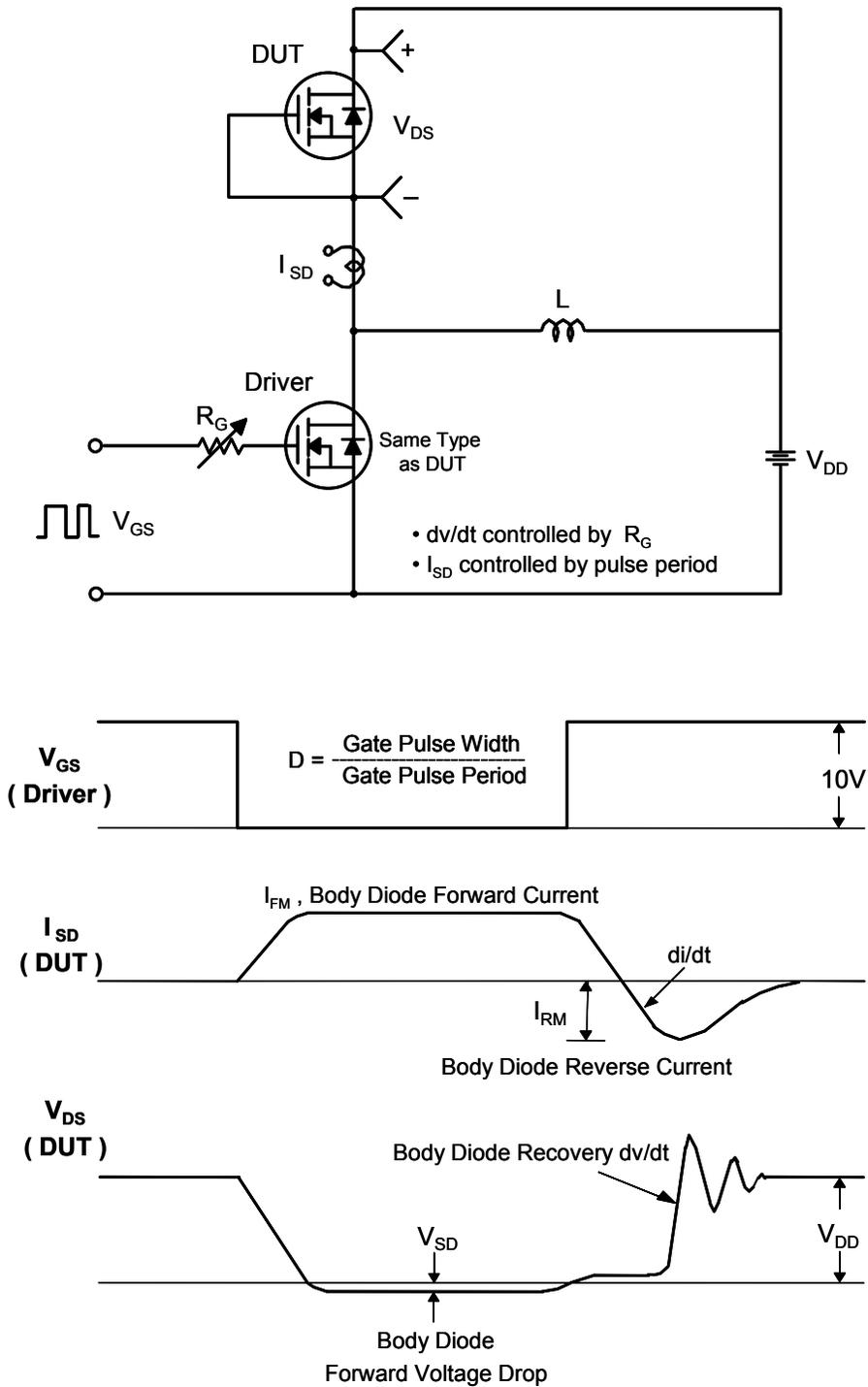


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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